High Power Probe Cards for engineering and production test – A survey.

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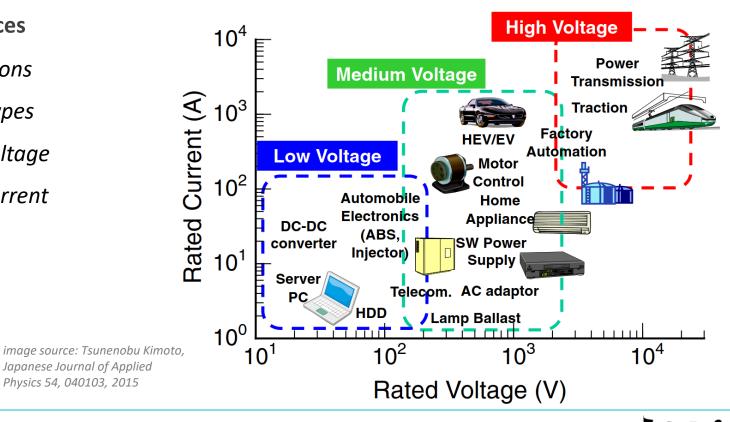
High Power Probe Cards

- **1**. Overview
- 2. Power devices Test requirements
- 3. High Voltage Probe Cards
- 4. High Temperature HV Probe Cards
- 5. High Current Probe Cards
- 6. Conclusion



Power devices

- Applications
- Device types
- Rated Voltage
- Rated Current





Typical production test requirements

- Reverse Voltage (Breakdown Voltage)
- Forward Current (On-state resistance)
- Reverse Current (Leakage Current at high reverse voltage)
- Dynamic switch test (max power dissipation) -> Up to several kA / kV



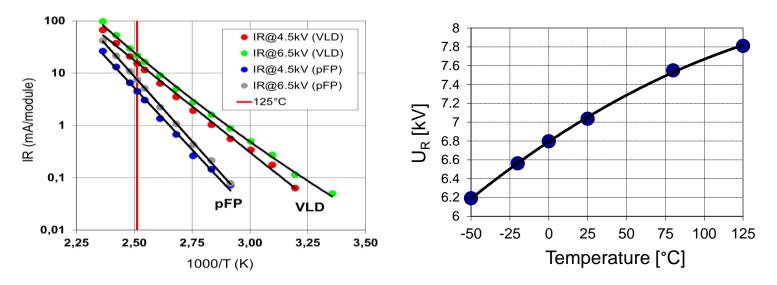
-> Up to several **kV**

-> Up to several **kA**

Typical engineering test requirements

Reverse current I_R for IGBTs with different termination structures as a function of temperature – at different Reverse voltages.

Reverse Voltage U_R as a function of temperature.



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Wafer Tests

- Production: Reverse Voltage
- Production: Reverse Current
- Production: Forward Current
- *Production:* Dynamic Switch
- Engineering: Reverse Voltage
- Engineering: Reverse Current
- Engineering: Dynamic Switch

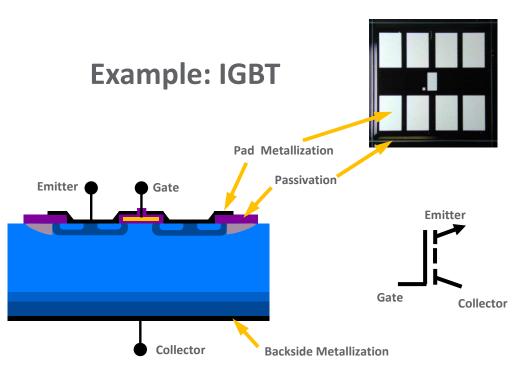
- -> High Voltage
- -> High Voltage
- -> High Current
- -> High Current & High Voltage
- -> High Voltage & High Temperature
- -> High Voltage & High Temperature
- -> High Current & High Voltage & High Temperature





Typical power devices

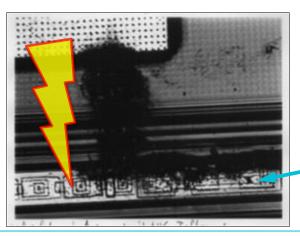
- Diodes
- Mosfet
- IGBT



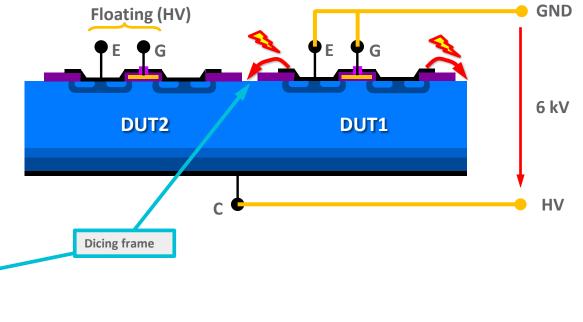


High Voltage test – Flash-over risk

- Test voltage higher than insulation strength of ambient air
- High discharge current
- Device damage



Reverse voltage test

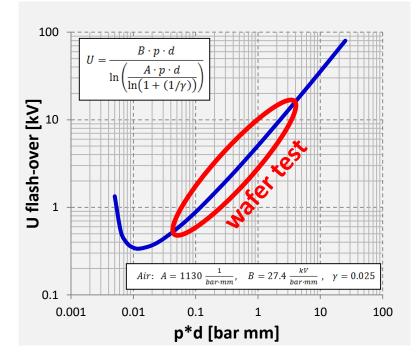




Flash-over suppression: theory

- Empirical Paschen law
- For breakdown strength of air
- breakdown voltage increases with pressure
- Higher pressure -> higher test voltage
- -> Safe test voltage rises appr. linearly with pressure!

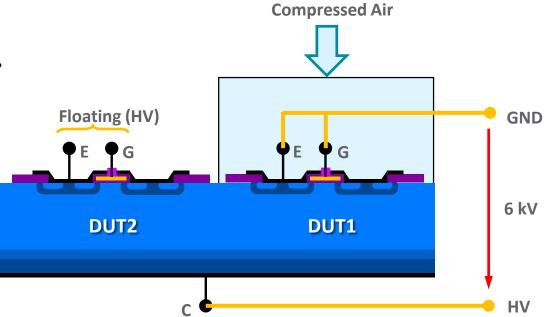
Paschen law





Flash-over suppression: principle

- Increase breakdown strength of air
- Local application of higher pressure
- Chip-scale pressure chamber





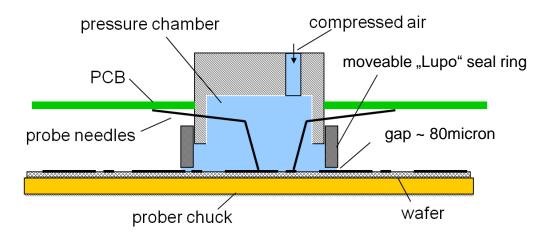


"Lupo" pressurized air chamber design

• Non-contact seal

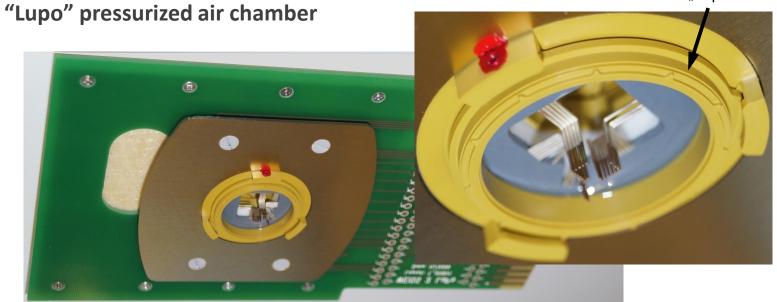
COMPASS

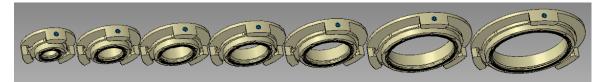
- Seal hovers above wafer
- Compressed Air expands in gap
- Air exhausts through gap
- Pressure constant over chamber





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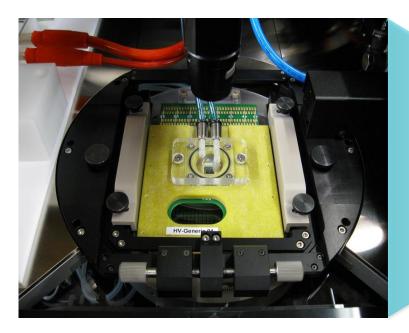






moveable "Lupo" seal ring

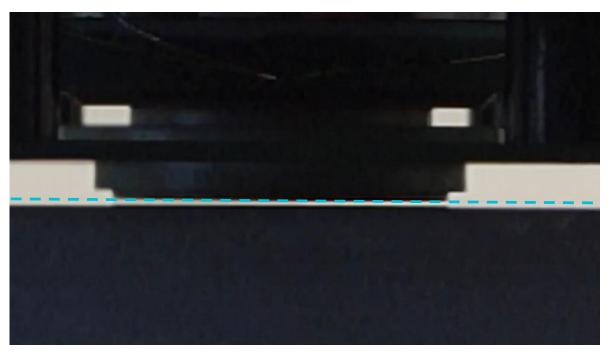
"Lupo" probe card in Tesla Prober







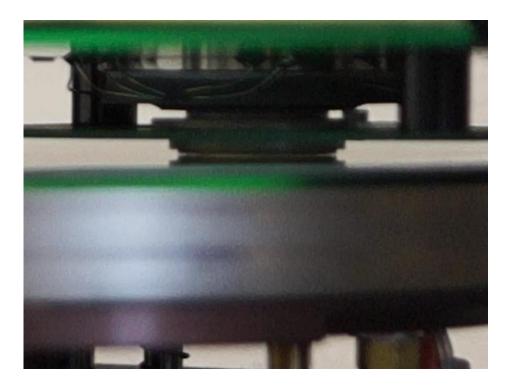
"Lupo" contactless operation







"Lupo" contactless operation

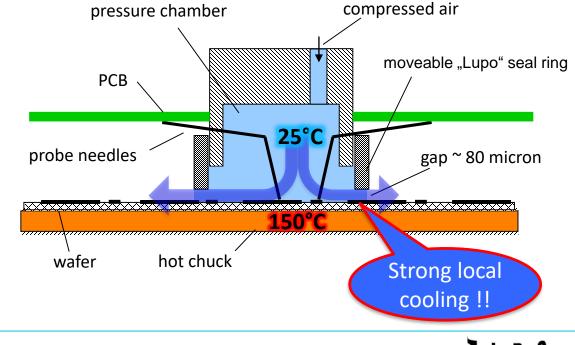






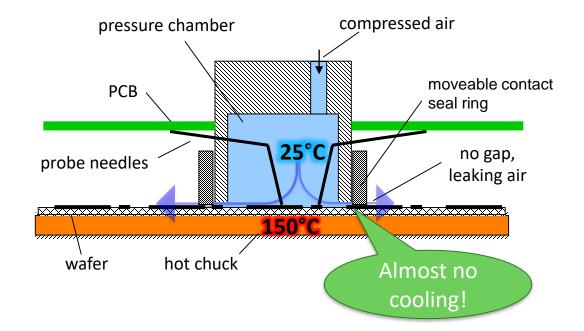
HV Wafer probing at higher temperatures

- Hot chuck 150°C
- TIPS Lupo air chamber
- Cooling effect on wafer
- Local cooling can disturb Chuck temperature control



HT Engineering Probe Cards

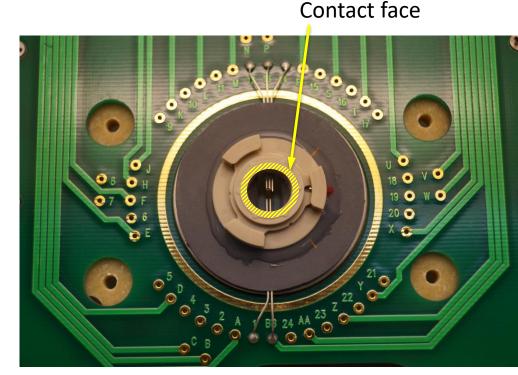
- device characterization and development
- hot wafer chuck 150°C
- compressed air 25°
- <u>Contact</u> Lupo seal :
 - -> low air flow
 - -> low cooling





HT Engineering Probe Cards

- Non-hovering air chamber seal
- Large flat contact surface
- Seal still moveable
- Seal adjusts to probe wear/overtravel



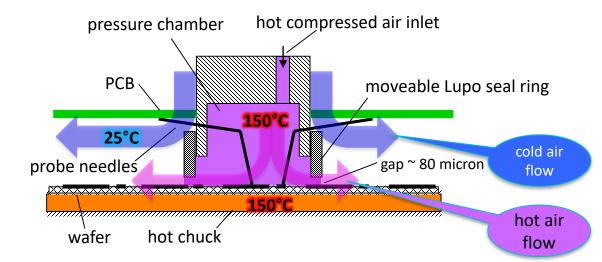


HT Production Probe Cards

- Hot compressed air supply
- dual hot-cold air stream to protect probe card

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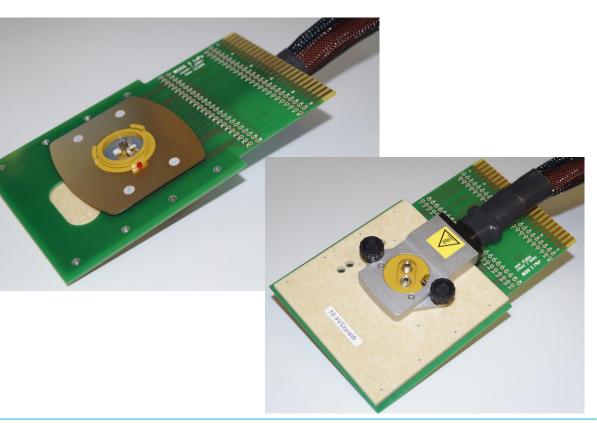
• reduced breakdown strength at higher temperatures





HT Production Probe Cards

- production wafer sort
- hot wafer chuck 150°C
- hot compressed air 150°
- non-contact Lupo seal







High Temperature Pressurized Air Supply

- Electrical heater
- Heats cold compressed air to 150°C
- closed-loop temperature control
- temperature sensor in probe card
- fast settling, stable operation
- integrated air cooling for probe card







Impact of Temperature on Breakdown Voltage

- Breakdown strength (Paschen law) for 25°C
- Hot air has lower density
 - -> pressure must be increased to get same breakdown strength
 - -> compensation factor is ratio of absolute temperatures

At 150°C -> 33% higher pressure needed!

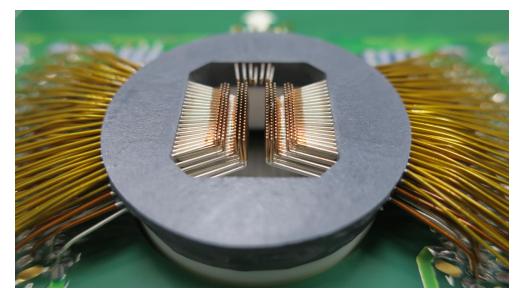
• Hot air stream: blows up to 600 W into prober prober thermal management!



High Current Probe Cards

High current test

- Forward current test
- Up to 1200 Ampere on a single die!
- Pulsed currents 5A/probe for 200µs
- Limiting: Probe tip heating
- Copper-Beryllium probes



IGBT, 1200 Ampere, 250 probes

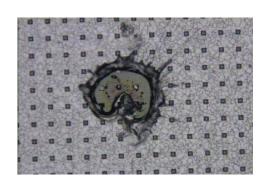




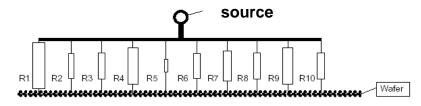
High Current Probe Cards

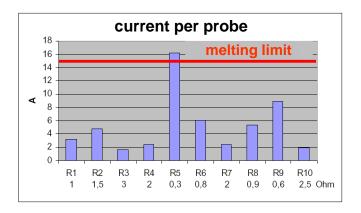
Challenges in high current testing

- Strong probe tip heating
- Heating depends on CRES
- Non-uniform current distribution
- Probe / tip overheating
- Pad melting!



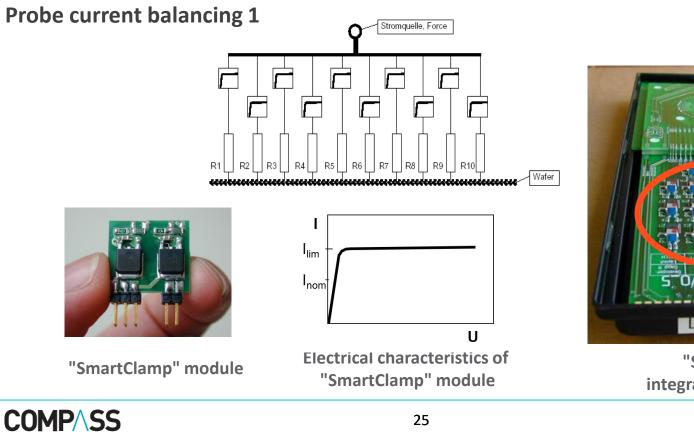
CRES per probe













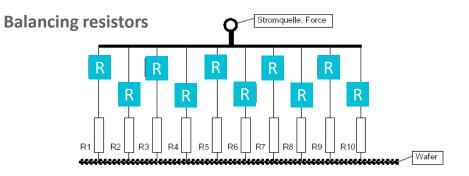
"SmartClamps" integrated on probe card

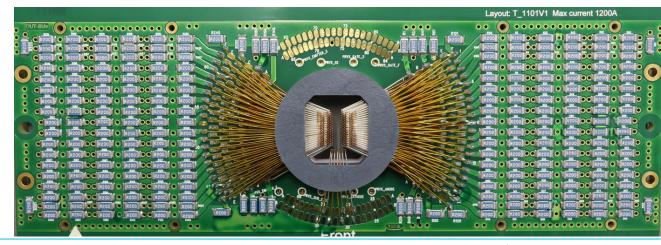


High Current Probe Cards

Probe current balancing 2

- For high pin counts / currents
- Resistors have value in range of CRES









- High power testing is feasible, limits pushed to 10kV / 1000A and beyond
- Trend to ever higher temperatures (125...150...175...200°C)
- Trend to production wafer sort at high temperatures
 - -> hot air testing is feasible but very costly
- Full coverage of test requirements is difficult to achieve, especially at higher temperatures
 - -> physics are imposing the limits
- We recommend to use "engineering" probe cards for highest temperature / voltage requirements





Thank You!

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